

45V NPN SMALL SIGNAL TRANSISTOR IN SOT23

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

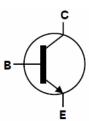
- BV_{CEO} > 45V
- I_C = 0.5A Continuous Collector Current
- I_{CM} = 1A Peak Pulse Current
- Complementary PNP Types: BC807-16
- Ideally Suited for Automatic Insertion
- Epitaxial Planar Die Construction
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

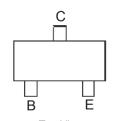
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



Top View



Device Symbol



Top View Pin-Out

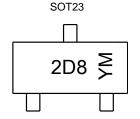
Ordering Information (Note 5)

Part number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
AC817-40Q-7	Automotive	2D8	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



2D8 = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: E = 2017)

M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	Е	F	G	Н		J	K	L	М	N	0	Р
	I -		I				ı	T -	T _	_		_
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	Ic	0.5	Α
Peak Collector Current	Ісм	1.0	Α
Peak Base Current	I _{BM}	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	ס	310	mW	
Power Dissipation	(Note 7)	P_{D}	350] !!!٧٧	
Thermal Resistance, Junction to Ambient	(Note 6)	5	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	357	C/VV	
Thermal Resistance, Junction to Leads	(Note 8)	$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-65 to +150	°C	

ESD Ratings (Note 9)

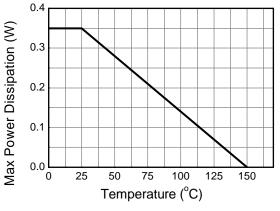
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

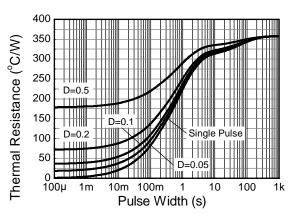
6. For a device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper; device is measured under still air

For a device mounted on minimum recommended pad layout FR-4 PCB with high conditions whilst operating in a steady-state.
Same as Note 6, except mounted on 15mm x 15mm 1oz copper.
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



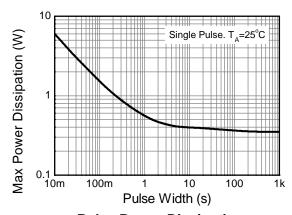
Thermal Characteristics and Derating Information





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	_	_	٧	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV_{CEO}	45	_	_	٧	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	_	_	٧	$I_{C} = 100 \mu A$
Collector-Emitter Cut-Off Current	lama			100	nA	$V_{CE} = 45V$
Collector-Emilier Cut-On Current	ICES			5.0	μΑ	$V_{CE} = 25V, T_J = +150$ °C
Emitter-Base Cut-Off Current	I _{EBO}		_	100	nA	$V_{EB} = 5.0V$
DC Current Gain (Note 10)	h	250		600		$V_{CE} = 1.0V, I_{C} = 100mA$
	h _{FE}	170	_	_		$V_{CE} = 1.0V, I_{C} = 300mA$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(SAT)}		_	0.7	٧	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Voltage (Note 10)	V_{BE}		_	1.2	٧	$V_{CE} = 1.0V, I_{C} = 300mA$
Gain Bandwidth Product	f⊤	100	_	_	MHz	$V_{CE} = 5.0V, I_{C} = 10mA,$ f = 50MHz
Collector-Base Capacitance	C _{CBO}	_	_	12	pF	$V_{CB} = 10V$, $f = 1.0MHz$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

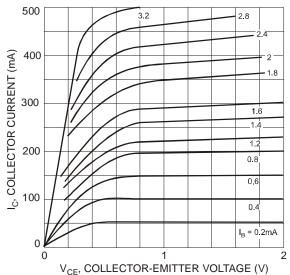


Figure 1 Typical Collector Current vs. Collector-Emitter Voltage

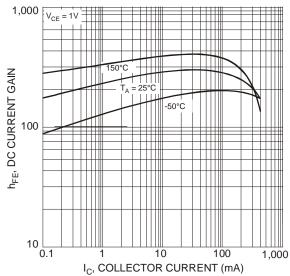


Figure 3 Typical DC Current Gain vs. Collector Current

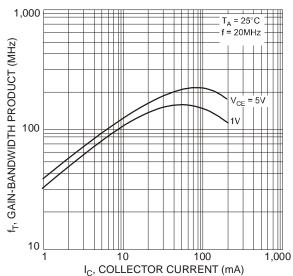


Figure 5 Gain-Bandwidth Product vs. Collector Current

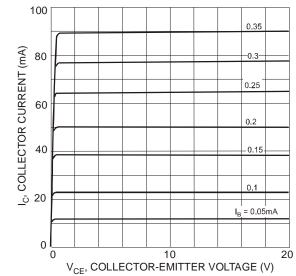


Figure 2 Typical Collector Current vs. Collector-Emitter Voltage

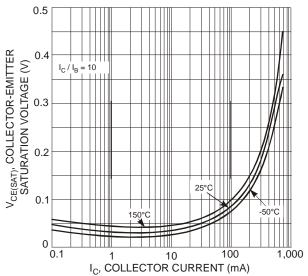


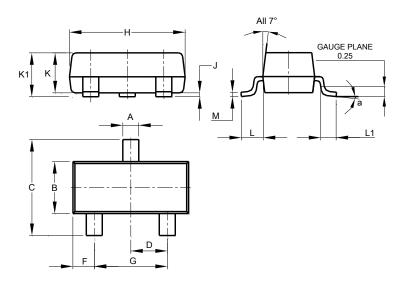
Figure 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

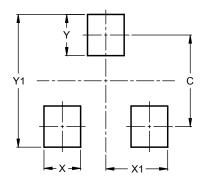


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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